BYC8-600P

Hyperfast power diode

24 July 2012

Product data sheet

1. Product profile

1.1 General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

1.2 Features and benefits

- Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

1.3 Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	SQW; $\delta = 0.5$; $T_{mb} \le 130$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	8	А
Static characte	eristics					
V _F	forward voltage	I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
Dynamic chara	acteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	12	18	ns





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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	}	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC8-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	SQW; $\bar{o} = 0.5$; $T_{mb} \le 130$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	8	А
I _{FRM}	repetitive peak forward current	SQW; δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le 130$ °C	-	16	Α
I _{FSM}	non-repetitive peak forward	SIN; $t_p = 10 \text{ ms}$; $T_{j(init)} = 25 ^{\circ}\text{C}$; Fig. 4	-	91	Α
	current	SIN; $t_p = 8.3 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; Fig. 4	-	100	Α
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

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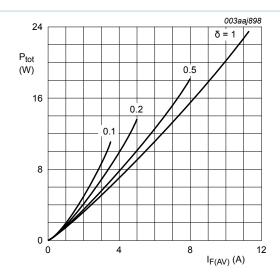


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 1.581 \text{ V; } R_{S} = 0.043 \text{ } \Omega \end{split}$$

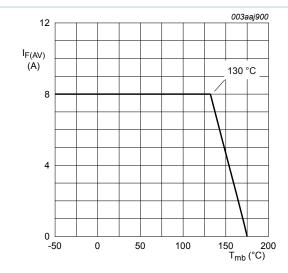


Fig. 3. Average forward current as a function of mounting base temperature; maximum values

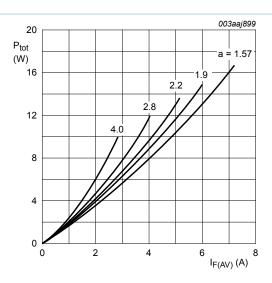


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

 $V_O = 1.581 \text{ V}; R_S = 0.043 \Omega$

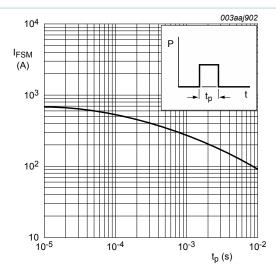


Fig. 4. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	2.5	K/W

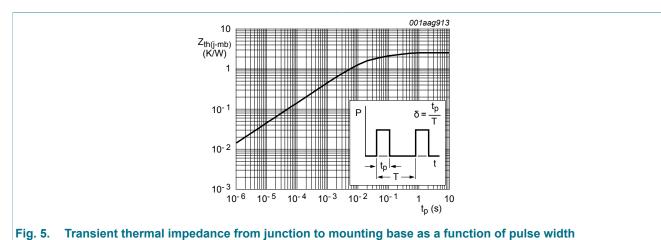
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

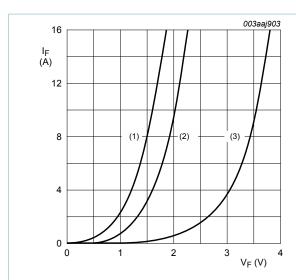


6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					_
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	20	μΑ
		V _R = 600 V; T _j = 125 °C	-	-	200	μΑ
Dynamic cl	haracteristics		1			
Q _r	recovered charge	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	17	-	nC
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	90	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	12	18	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	2.2	Α
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	6	А

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(1) $T_j = 125$ °C; typical values; (2) $T_j = 125$ °C; maximum values; (3) $T_j = 25$ °C; maximum values; $V_O = 1.581$ V; $R_S = 0.043$ Ω

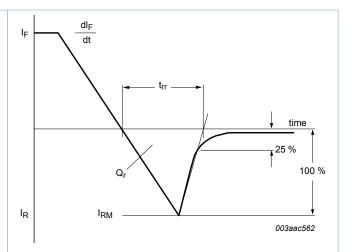


Fig. 7. Reverse recovery definitions; ramp recovery

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7. Package outline

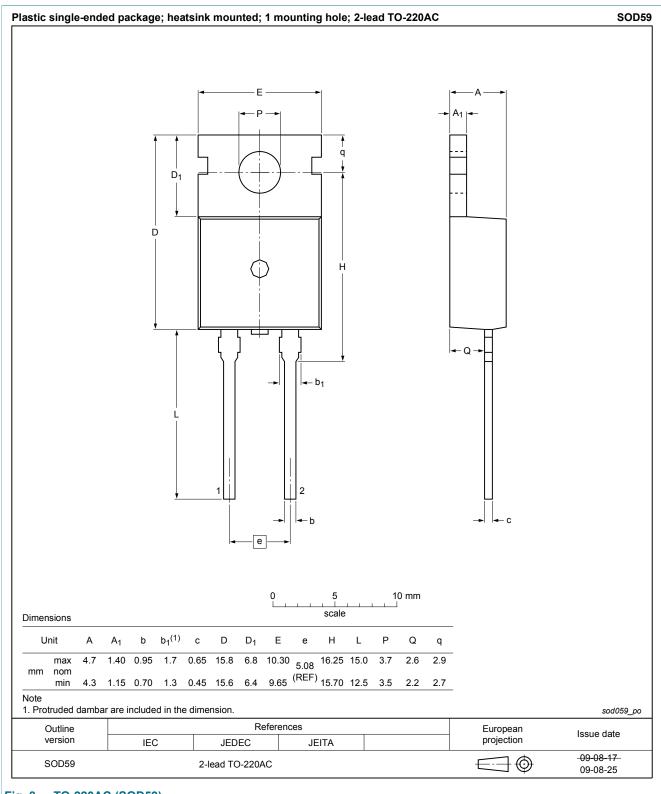


Fig. 8. TO-220AC (SOD59)

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8. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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